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June 2014

FQA30N40

N-Channel QFET® MOSFET

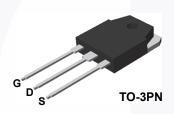
400 V, 30 A, 140 mΩ

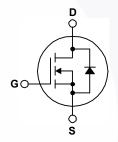
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- 30 A, 400 V, $R_{DS(on)}$ = 140 m Ω (Max.) @ V_{GS} = 10 V, I_D = 15 A
- Low Gate Charge (Typ. 90 nC)
- Low Crss (Typ. 60 pF)
- 100% Avalanche Tested





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter		FQA30N40	Unit
V_{DSS}	Drain-Source Voltage		400	V
I _D	Drain Current - Continuous (T _C = 25°C	;)	30	Α
	- Continuous (T _C = 100°	C)	19	A
I _{DM}	Drain Current - Pulsed	(Note 1)	120	A
V _{GSS}	Gate-Source Voltage		± 30	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	1400	mJ
I _{AR}	Avalanche Current	(Note 1)	30	Α
E _{AR}	Repetitive Avalanche Energy	(Note 1)	29	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3		4.5	V/ns
P _D	Power Dissipation (T _C = 25°C)		290	W
	- Derate above 25°C		2.33	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FQA30N40	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.43	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

Package Marking and Ordering Information

Device Marking Device		Package	Reel Size	Tape Width	Quantity	
FQA30N40	FQA30N40	TO-3PN	-	-	30	

Electrical Characteristics

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	400			V
ΔBV_{DSS} / ΔT_{J}	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.4		V/°C
I _{DSS}	Zoro Coto Valtoro Droin Current	V _{DS} = 400 V, V _{GS} = 0 V			1	μΑ
	Zero Gate Voltage Drain Current	V _{DS} = 320 V, T _C = 125°C			10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Cha	aracteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 15 A		0.107	0.14	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 50 V, I _D = 15 A		20		S
Dynam	ic Characteristics					
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V,		3400	4400	pF
^	Outrot Considerate	50 . 00		580	750	nΕ
Coss	Output Capacitance	f = 1.0 MHz		300	750	pF

Switching Characteristics

	_						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 200 V, I _D = 30 A,		-	80	170	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$		-	320	650	ns
t _{d(off)}	Turn-Off Delay Time	· · · · · · · · · · · · · · · · · ·		-	190	390	ns
t _f	Turn-Off Fall Time	(Note	4)	-	170	350	ns
Q_g	Total Gate Charge	V _{DS} = 320 V, I _D = 30 A,		/	90	120	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V		-	22		nC
Q _{gd}	Gate-Drain Charge	(Note	4)	-	46		nC

Drain-Source Diode Characteristics and Maximum Ratings

	· · · · · · · · · · · · · · · · · · ·					
I _S	Maximum Continuous Drain-Source Diode Forward Current				30	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				120	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 30 A			1.5	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V, } I_{S} = 30 \text{ A,}$		370	/	ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs		3.9		μC

- Notes: 1. Repetitive Rating : Pulse width limited by maximum junction temperature 2. L = 2.7mH, I $_{AS}$ = 30A, V $_{DD}$ = 50V, R $_{G}$ = 25 Ω , Starting T $_{J}$ = 25°C 3. I $_{SD}$ \leq 30A, di/dt \leq 200A/µs, V $_{DD}$ \leq BV $_{DSS}$, Starting T $_{J}$ = 25°C 4. Essentially independent of operating temperature

Typical Characteristics

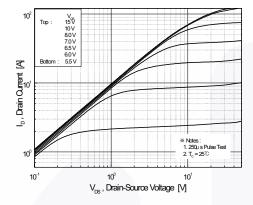


Figure 1. On-Region Characteristics

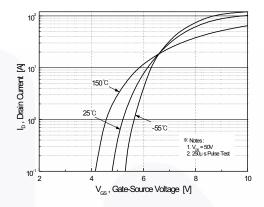


Figure 2. Transfer Characteristics

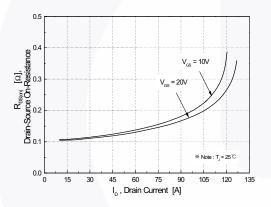


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

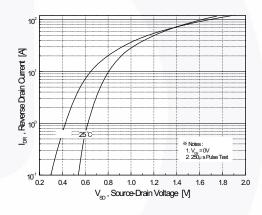


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

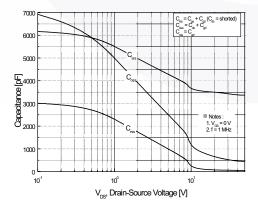


Figure 5. Capacitance Characteristics

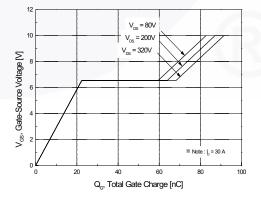


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

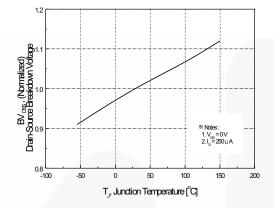


Figure 7. Breakdown Voltage Variation vs. Temperature

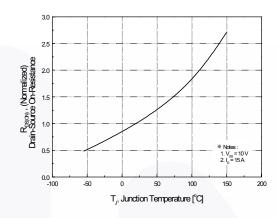


Figure 8. On-Resistance Variation vs. Temperature

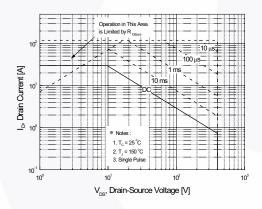


Figure 9. Maximum Safe Operating Area

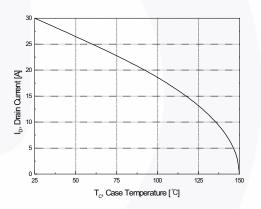


Figure 10. Maximum Drain Current vs. Case Temperature

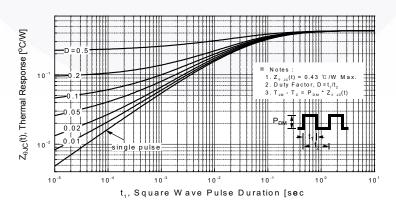


Figure 11. Transient Thermal Response Curve



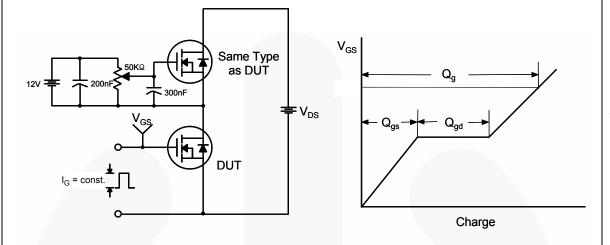


Figure 13. Resistive Switching Test Circuit & Waveforms

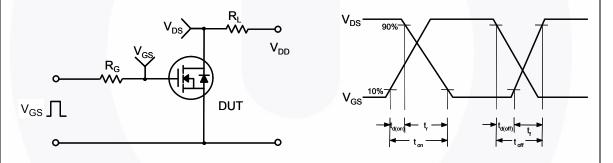
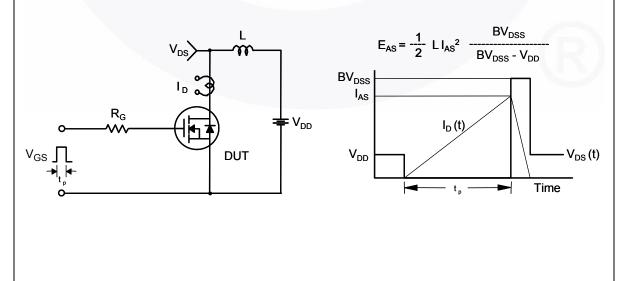
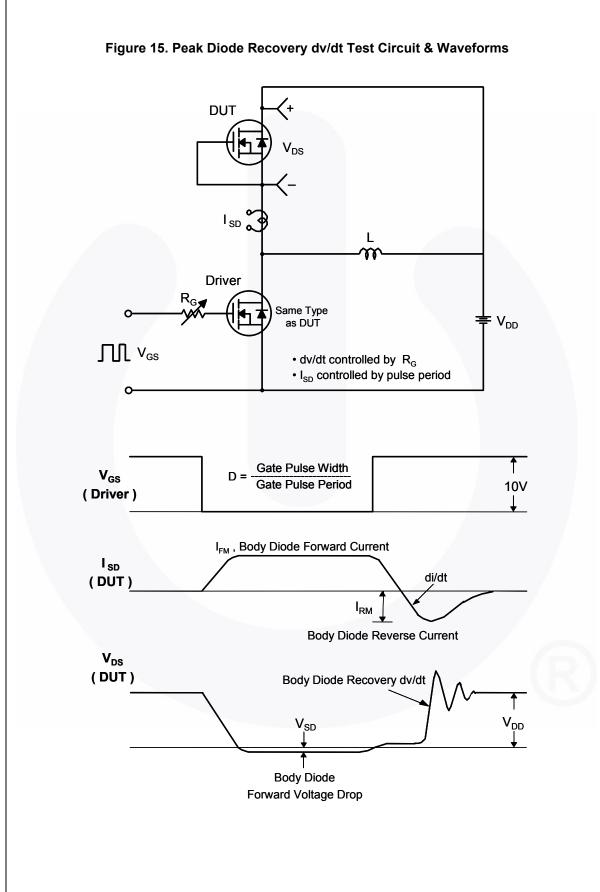


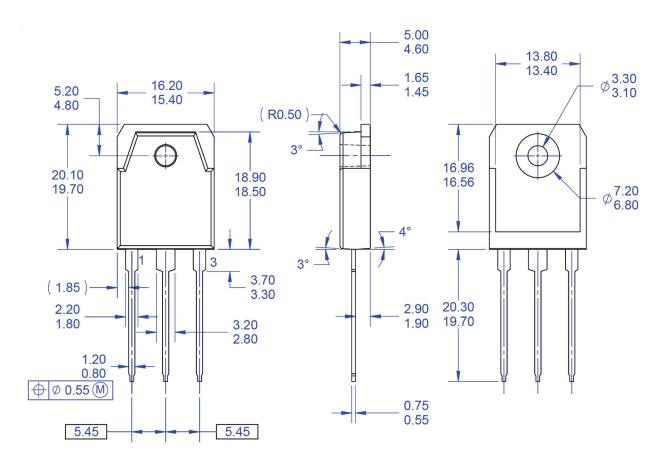
Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms





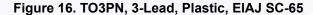
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Mechanical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED

- A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.
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- DIMENSION AND TOLERANCING PER ASME14.5-2009.
- D) DIMENSIONS ARE EXCLUSSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSSIONS.
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